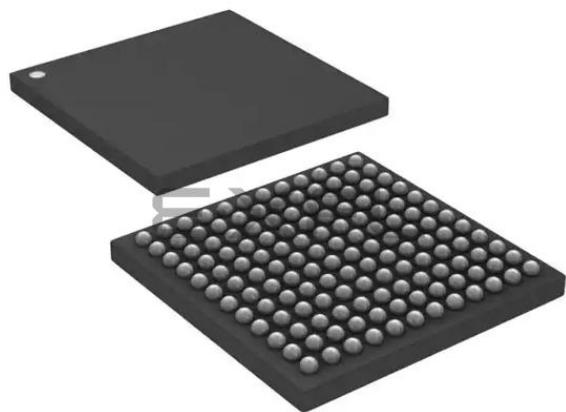




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	112
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str735fz2h6

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clock/calendar/alarm function. When the STR73xF is in LPWFI mode the RTC keeps running, powered by the low power voltage regulator.

UARTs

The 4 UARTs allow full duplex, asynchronous, communications with external devices with independently programmable TX and RX baud rates up to 625 Kbaud.

Buffered serial peripheral interfaces (BSPI)

Each of the three BSPIs allow full duplex, synchronous communications with external devices, master or slave communication at up to 6 Mb/s in master mode and up to 4.5 Mb/s in slave mode (@36 MHz system clock).

I²C interfaces

The two I²C Interfaces provide multi-master and slave functions, support normal and fast I²C mode (400 kHz) and 7 or 10-bit addressing modes.

A/D converter

The 10-bit analog to digital converter, converts up to 16 channels in single-shot or continuous conversion modes (12 channels in 100-pin devices). The minimum conversion time is 3 μ s.

Watchdog

The 16-bit watchdog timer protects the application against hardware or software failures and ensures recovery by generating a reset.

I/O ports

Up to 112 I/O ports (72 in 100-pin devices) are programmable as general purpose input/output or alternate function.

External interrupts and wake-up lines

16 external interrupts lines are available for application use. In addition, up to 32 external Wake-up lines (18 in 100-pin devices) can be used as general purpose interrupts or to wake-up the application from STOP mode.

3.1 Related documentation

Available from www.arm.com:

ARM7TDMI technical reference manual

Available from <http://www.st.com>:

STR73x reference manual (RM0001)

STR7 Flash programming reference manual

STR73x software library user manual

For a list of related application notes refer to <http://www.st.com>.

Table 4. STR73xF pin description

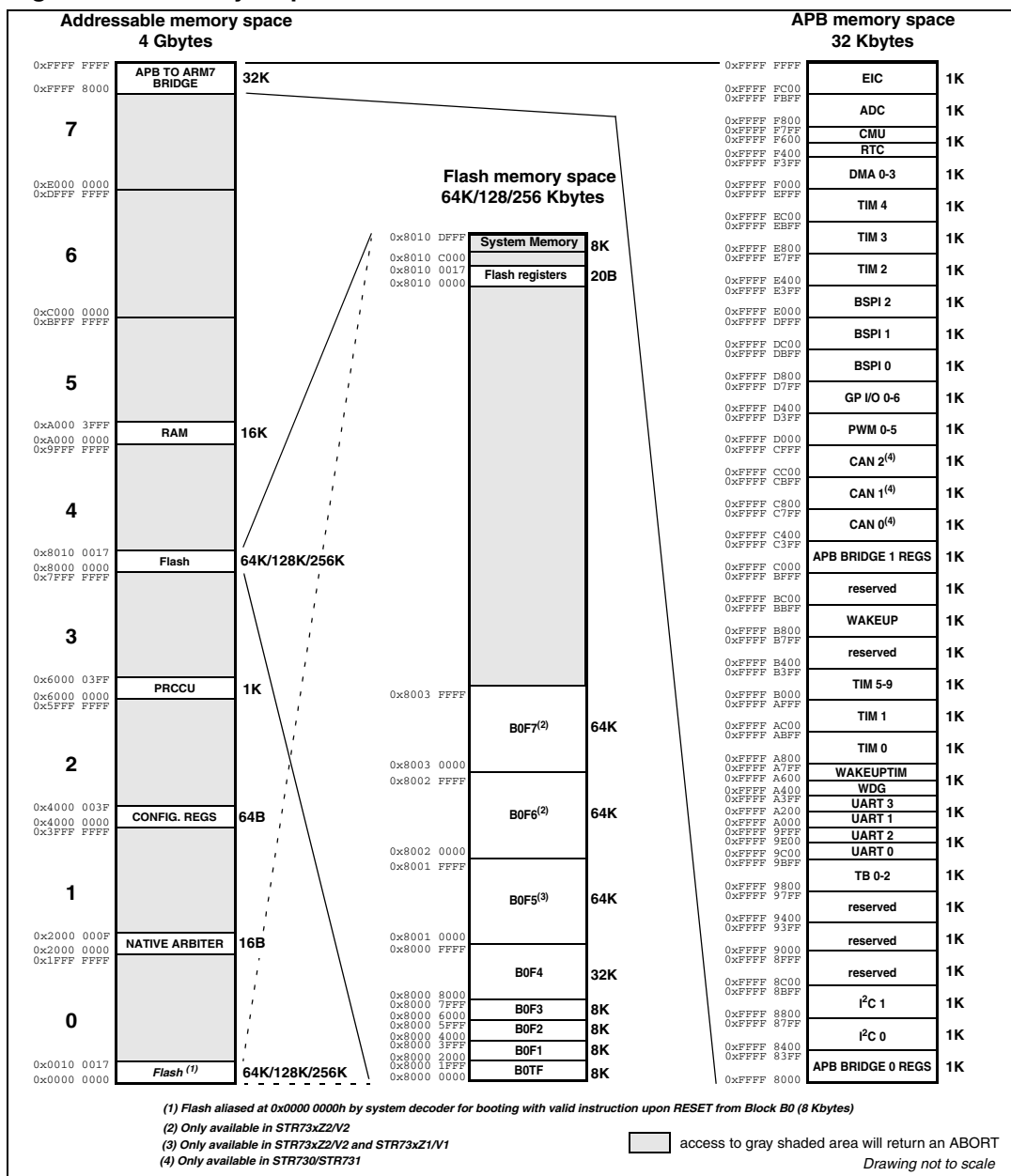
Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
97	F9		P4.3/ICAPB8	I/O	T _T		WUP27	2mA	X	X	Port 4.3	TIM8: input capture B input
98	F8		P4.4/CAN2TX	I/O	T _T			2mA	X	X	Port 4.4	CAN2: transmit data output
99	E12		P4.5/CAN2RX	I/O	T _T		WUP18	2mA	X	X	Port 4.5	CAN2: receive data input
100	E11	72	P4.6/SCL1	I/O	T _T		WUP19	2mA	X	X	Port 4.6	I2C1: serial clock
101	C12	73	P4.7/SDA1	I/O	T _T			2mA	X	X	Port 4.7	I2C1: serial data
102	B12		P4.8/OCMPA8	I/O	T _T			2mA	X	X	Port 4.8	TIM8: output compare A output
103	E10		P4.9/ICAPB6	I/O	T _T			2mA	X	X	Port 4.9	TIM6: input capture B input
104	E9	74	P4.10/ICAPA6/ CAPB5	I/O	T _T		WUP20	2mA	X	X	Port 4.10	TIM6: input capture A input (144-pin pkg only) TIM5: input capture B input (TQFP100 only)
105	D12		P4.11/OCMPB8	I/O	T _T			2mA	X	X	Port 4.11	TIM8: output compare B output
106	D11		P4.12/ICAPA9	I/O	T _T		WUP21	2mA	X	X	Port 4.12	TIM9: input capture A input
107	D10		P4.13/ICAPB9	I/O	T _T			2mA	X	X	Port 4.13	TIM9: input capture B input
108	C11	75	P4.14/ $\overline{SS}$ 1	I/O	T _T			2mA	X	X	Port 4.14	BSPI1: slave select
109	B11	76	P4.15/SCK1	I/O	T _T		WUP22	2mA	X	X	Port 4.15	BSPI1: serial clock
110	B10	77	P5.0/MOSI1	I/O	T _T			2mA	X	X	Port 5.0	BSPI1: master output/slave input
111	C10	78	P5.1/MISO1	I/O	T _T			2mA	X	X	Port 5.1	BSPI1: master input/Slave output
112	A9		P5.2/OCMPA9	I/O	T _T			2mA	X	X	Port 5.2	TIM9: output compare A output
113	B9		P5.3/OCMPB9	I/O	T _T			2mA	X	X	Port 5.3	TIM9: output compare B output
114	C9	79	P5.4/ $\overline{SS}$ 2/PWM3	I/O	T _T			2mA	X	X	Port 5.4	BSPI2: slave select PWM3: PWM output (TQFP100 only)
115	D9	80	P5.5/SCK2	I/O	T _T		WUP23	2mA	X	X	Port 5.5	BSPI2: serial clock
116	A11	81	P5.6/MOSI2	I/O	T _T			2mA	X	X	Port 5.6	BSPI2: master output/slave input
117	A10	82	P5.7/MISO2	I/O	T _T			2mA	X	X	Port 5.7	BSPI2: master input/slave output
118	A8	83	P5.8/PWM4	I/O	T _T		INT6	2mA	X	X	Port 5.8	PWM4: PWM output (TQFP100 only)

3.3 Memory mapping

Figure 5 shows the various memory configurations of the STR73xF system. The system memory map (from 0x0000_0000 to 0xFFFF_FFFF) is shown on the left part of the figure, the right part shows maps of the Flash and APB areas. For flexibility the Flash or RAM addresses can be aliased to Block 0 addresses using the remapping feature

Most reserved memory spaces (gray shaded areas in Figure 5) are protected from access by the user code. When an access this memory space is attempted, an ABORT signal is generated. Depending on the type of access, the ARM processor will enter “prefetch abort” state (Exception vector 0x0000_000C) or “data abort” state (Exception vector 0x0000_0010). It is up to the application software to manage these abort exceptions.

Figure 5. Memory map



4 Electrical parameters

4.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS} .

4.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A=25^\circ\text{C}$ and $T_A=T_{Amax}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\Sigma$).

4.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A=25^\circ\text{C}$ and $V_{DD}=5\text{ V}$. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\Sigma$).

4.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

4.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 6](#).

4.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 7](#).

Figure 6. Pin loading conditions

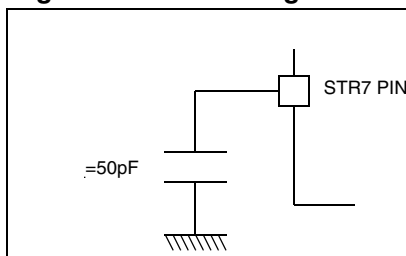
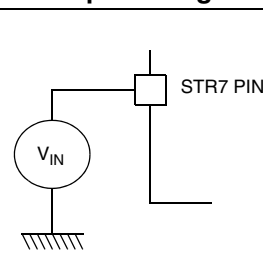


Figure 7. Pin input voltage



4.2 Absolute maximum ratings

Stresses above those listed as “absolute maximum ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 5. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD} - V_{SS}$	External 5 V Supply voltage	-0.3	6.0	v
V_{SSA}	Reference ground for A/D converter	V_{SS}	V_{SS}	v
$V_{DDA} - V_{SSA}$	Reference voltage for A/D converter	-0.3	$V_{DD}+0.3$	V
V_{IN}	Input voltage on any pin	-0.3	$V_{DD}+0.3$	
$ ΔV_{DDx} $	Variations between different 5 V power pins	-	0.3	mV
$ V_{SSx} - V_{SS} $	Variations between all the different ground pins	-	0.3	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	see : Absolute maximum ratings (electrical sensitivity) on page 36		
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)			

Table 6. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power lines (source) ¹⁾	100	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink) ¹⁾	100	
I_{IO}	Output current sunk by any I/O and control pin	10	
	Output current source by any I/O and control pin	10	
$I_{INJ(PIN)}^{2) \& 3)}$	Injected current on any other pin ⁴⁾ & ⁵⁾	±10	
$ΣI_{INJ(PIN)}^{2)}$	Total injected current (sum of all I/O and control pins) ⁴⁾	±75	

1. All 5 V power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external 5 V supply
2. $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$.
3. Negative injection disturbs the analog performance of the device. See note in [Section 4.3.6: 10-bit ADC characteristics on page 43](#).
4. When several inputs are submitted to a current injection, the maximum $ΣI_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with $ΣI_{INJ(PIN)}$ maximum current injection on four I/O port pins of the device.
- 5.) In 144-pin devices, only +10 mA on P0.3, P1.13, P3.6 and P4.13 pins (negative injection not allowed).

Typical application current consumption

Table 11. Typical consumption in Run mode at 25°C and 85°C

Conditions		f _{MCLK} (MHz)	f _{ADC} (MHz)	Typical I _{DD} (mA)
V _{DD} = 5.5 V, RC oscillator off, PLL on, RTC enabled, 1 Timer (TIM) running, and ADC running in scan mode.	Code executing in RAM	10	10	20
		20		29
		36	9	42
	Code executing in Flash	10	10	22
		20		32
		36	9	48

Table 12. Typical consumption in Run and low power modes at 25°C

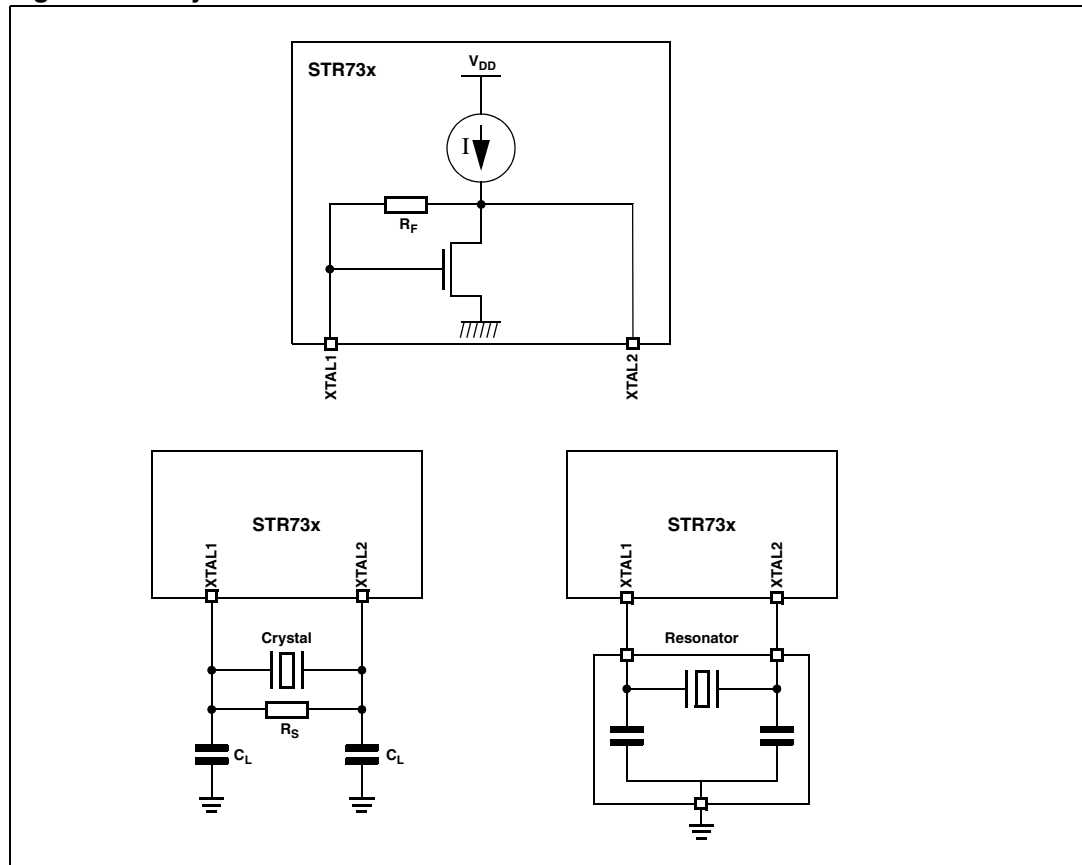
Mode	Conditions	f _{MCLK}	Typical I _{DD}
RUN	All peripherals on, RAM execution	36 MHz	76 mA
		24 MHz	56 mA
WFI	Main voltage regulator on, Flash on, EIC on, WIU on, GPIOs on.	36 MHz	33 mA
		24 MHz	31 mA
SLOW	PLL off, main voltage regulator on	4 MHz	11 mA
	CLOCK2/16, main voltage regulator on	250 kHz	8 mA
	CLOCK2/16, main voltage regulator off	250 kHz	3 mA
	RC oscillator running in low frequency, main crystal oscillator off, main voltage regulator off	29 kHz	2.5 mA
LPWFI	CLOCK2/16, main voltage regulator off, LP voltage regulator = 2 mA, Flash in power down mode.	250 kHz	528 µA
STOP	Main voltage regulator off, RTC on, RC oscillator off, LP voltage regulator = 6 mA	-	378 µA
	Main voltage regulator off, RTC off, RC oscillator off, LP voltage regulator = 6 mA	-	83 µA
	Main voltage regulator off, RTC off, RC oscillator off, LP voltage regulator = 4 mA	-	64 µA
	Main voltage regulator off, RTC off, RC oscillator off, LP voltage regulator = 2 mA	-	44 µA
HALT	RTC off, LP voltage regulator = 2 mA	-	44 µA

4.3.2 Clock and timing characteristics

Crystal / ceramic resonator oscillator

The STR73xF can operate with a crystal oscillator or resonator clock source. [Figure 12](#) describes a simple model of the internal oscillator driver as well as example of connection for an oscillator or a resonator.

Figure 12. Crystal oscillator and resonator



- Note:
- 1 XTAL2 must not be used to directly drive external circuits.
 - 2 For test or boot purpose, XTAL2 can be used as an high impedance input pin to provide an external clock to the device. XTAL1 should be grounded, and XTAL2 connected to a wave signal generator providing a 0 to VDD signal. Directly driving XTAL2 may results in deteriorated jitter and duty cycle.

Main oscillator characteristics

$V_{DD} = 5\text{ V} \pm 10\%$, $T_A = -40^\circ\text{C}$ to T_{Amax} , unless otherwise specified.

Table 14. Main oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{OSC}	Oscillator frequency		4		8	MHz
g_m	Oscillator transconductance		1.5		4.2	mA/V
$V_{OSC}^{1)}$	Oscillation amplitude	$f_{OSC} = 4\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	2.4	-	V
		$f_{OSC} = 8\text{ MHz}$, $T_A = 25^\circ\text{C}$		1.-		
$V_{AV}^{1)}$	Oscillator operating point	Sine wave middle, $T_A = 25^\circ\text{C}$	-	0.77	-	v
$t_{STUP}^{1)}$	Oscillator start-up time	External crystal, $V_{DD} = 5.5\text{ V}$, $f_{OSC} = 4\text{ MHz}$, $T_A = -40^\circ\text{C}$	-	-	12	ms
		External crystal, $V_{DD} = 5.0\text{ V}$, $f_{OSC} = 4\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	5.5	-	ms
		External crystal, $V_{DD} = 5.5\text{ V}$, $f_{OSC} = 6\text{ MHz}$, $T_A = -40^\circ\text{C}$	-	-	8	ms
		External crystal, $V_{DD} = 5.0\text{ V}$, $f_{OSC} = 6\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	3.3	-	ms
		External crystal, $V_{DD} = 5.5\text{ V}$, $f_{OSC} = 8\text{ MHz}$, $T_A = -40^\circ\text{C}$	-	-	7	ms
		External crystal, $V_{DD} = 5.0\text{ V}$, $f_{OSC} = 8\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	2.7	-	ms

RC/backup oscillator characteristics

$V_{DD} = 5V \pm 10\%$, $T_A = -40^\circ\text{C}$ to T_{Amax} , unless otherwise specified.

Table 15. RC oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{RC}	RC frequency	High frequency mode ¹⁾		2.35		MHz
		Low frequency mode ¹⁾		29		kHz
f_{RCHF}	RC high frequency	CMU_RCCTL = 0x0	3			MHz
		CMU_RCCTL = 0xF			2.3	MHz
f_{RCLF}	RC low frequency	CMU_RCCTL = 0x0	35			kHz
		CMU_RCCTL = 0xF			30	kHz
$f_{RCHFS}^{2)}$	RC high frequency stability	Fixed CMU_RCCTL			10	%
$f_{RCLFS}^{2)}$	RC low frequency stability	Fixed CMU_RCCTL			23	%
t_{RCSTUP}	RC start-up time	Stable V_{DD} , $f_{RC} = 2.35\text{ MHz}$, $T_A = 25^\circ\text{C}$		2.35		μs

1) CMU_RCCTL = 0x8

2) RC frequency shift versus average value (%)

PLL electrical characteristics

$V_{DD} = 5\text{ V} \pm 10\%$, $T_A = -40^\circ\text{C}$ to T_{Amax} , unless otherwise specified

Table 16. PLL characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
$f_{PLLIN}^{(1)}$	PLL reference clock	FREF_RANGE = '0' FREF_RANGE = '1'	1.5 3.0		3.0 5.0	MHz
f_{PLLOUT}	PLL output clock	MX = "00" MX = "01" MX = "10" MX = "11"	20 x f_{PLLIN} 12 x f_{PLLIN} 28 x f_{PLLIN} 16 x f_{PLLIN}			MHz
f_{MCLK}	System clock	DX = 1..7	f_{PLLOUT}/DX		36	MHz
$f_{FREE}^{(2)}$	PLL free running frequency	FREF_RANGE = '0', MX0 = '1' FREF_RANGE = '0', MX0 = '0' FREF_RANGE = '1', MX0 = '1' FREF_RANGE = '1', MX0 = '0'		120 240 240 480		kHz
$t_{LOCK}^{(3)}$	PLL lock time	Stable oscillator ($f_{PLLIN} = 4\text{ MHz}$), stable V_{DD}		100	300	μs
Δt_{PKJIT}	PLL jitter (pk to pk)	$f_{PLLIN} = 4\text{ MHz}$ (pulse generator)			1.5	ns

1. f_{PLLIN} is obtained from f_{OSC} directly or through an optional divider by 2.

2. Typical data are based on $T_A = 25^\circ\text{C}$, $V_{DD} = 5\text{V}$

3. Max value is guaranteed by characterization, not tested in production.

Table 17. Low-power mode wake-up timing

Symbol	Parameter	Conditions	Typ	Unit
t_{WUHALT}	Wake-up from HALT mode		200	μs
t_{WUSTOP}	Wake-up from STOP mode	RC high frequency in STOP mode	180	μs
		RC low frequency in STOP mode	234	μs
$t_{WULPWF1}^{1)}$	Wake-up from LPWFI mode	Main voltage regulator on RC oscillator off $f_{OSC} = 4\text{ MHz}$, $f_{MCLK} = f_{OSC}/16$ RAM or FLASH execution	27	μs
		Main voltage regulator on RC oscillator = high frequency Flash execution	46	μs
		Main voltage regulator on RC oscillator = low frequency Flash execution	3.6	ms

1. Flash memory programmed to enter Power Down mode during LPWFI.

4.3.5 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 23. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage ¹⁾	TTL ports			0.8	V
V_{IH}	Input high level voltage ¹⁾		2.0			
$I_{INJ(PIN)}$	Injected current on any I/O pin				± 10	mA
$\Sigma I_{INJ(PIN)}$ ²⁾	Total injected current (sum of all I/O and control pins)				± 75	mA
I_{lkg}	Input leakage current ³⁾	$V_{SS} \leq V_{IN} \leq V_{DD}$			± 1	μA
I_S	Static current consumption ⁴⁾	Floating input mode		200		μA
R_{PU}	Weak pull-up equivalent resistor ⁵⁾	$V_{IN} = V_{SS}$	55	120	220	$k\Omega$
R_{PD}	Weak pull-down equivalent resistor ⁵⁾	$V_{IN} = V_{DD}$	55	120	220	$k\Omega$
C_{IO}	I/O pin capacitance			5		pF

1. Data based on characterization results, not tested in production.
2. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to $I_{INJ(PIN)}$ specification. A positive injection is induced by $V_{IN} > V_{33}$ while a negative injection is induced by $V_{IN} < V_{SS}$. Refer to [Section 4.2 on page 22](#) for more details.
3. Leakage could be higher than max. if negative current is injected on adjacent pins.
4. Configuration not recommended, all unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor. Data based on design simulation and/or technology characteristics, not tested in production.
6. The R_{PU} pull-up and R_{PD} pull-down equivalent resistor are based on a resistive transistor (corresponding I_{PU} and I_{PD} current characteristics described in [Figure 19](#)).

Figure 15. V_{OH} JTDO pin vs I_{OL} @ V_{DD} 5 V

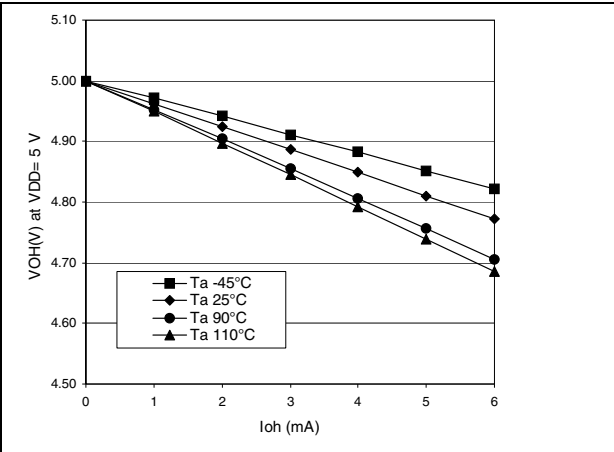


Figure 16. V_{OL} JTDO pin vs I_{OL} @ V_{DD} 5 V

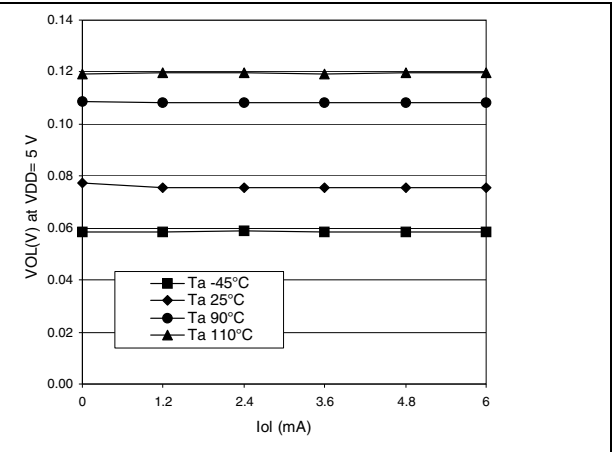


Figure 17. V_{OH} P6.0 pin vs I_{OL} @ V_{DD} 5 V

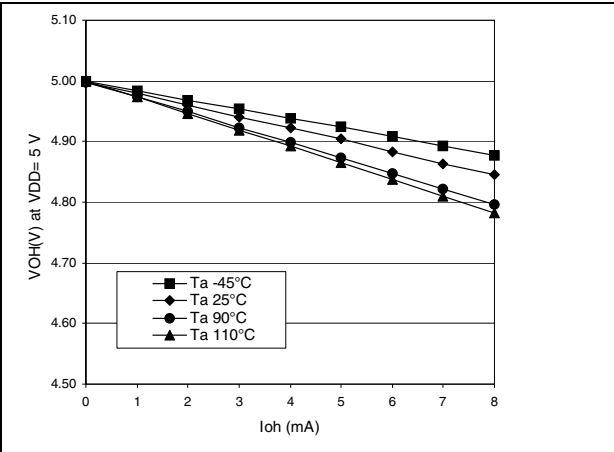


Figure 18. V_{OL} P6.0 pin vs I_{OL} @ V_{DD} 5 V

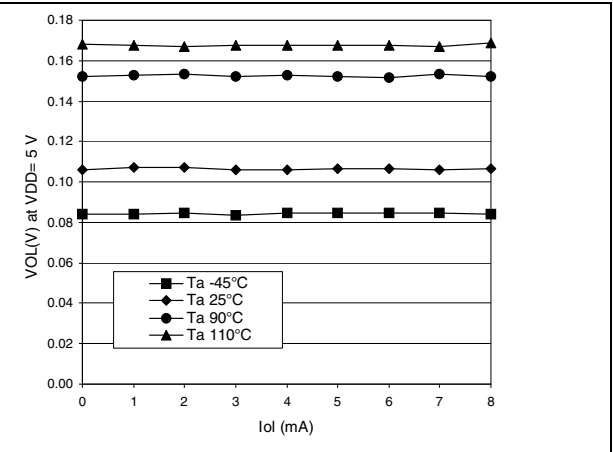


Figure 20. NRSTIN R_{PU} vs. V_{DD}

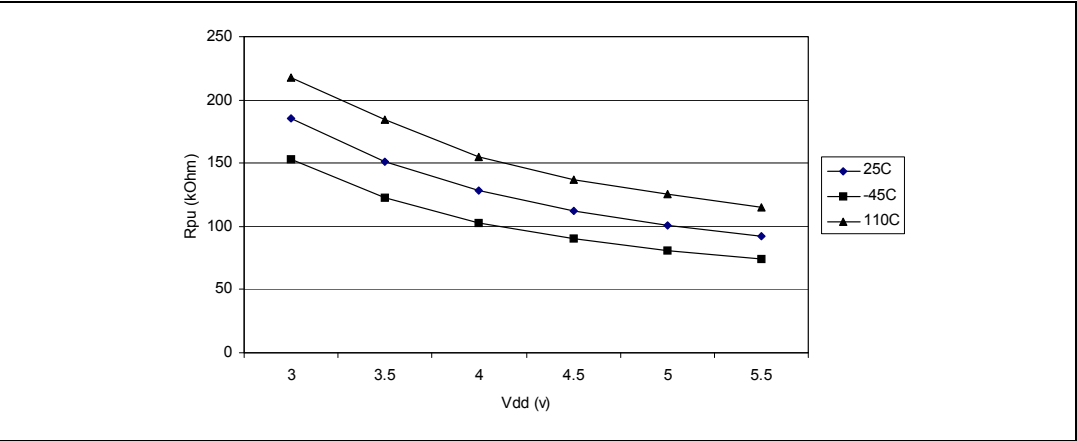


Table 27. ADC accuracy with $f_{MCLK} = 20\text{ MHz}$, $f_{ADC} = 10\text{ MHz}$, $R_{AIN} < 10\text{ k}\Omega$, R_{AIN} , $V_{DDA} = 5\text{ V}$. This assumes that the ADC is calibrated²⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
$ E_T $	Total unadjusted error ¹⁾		1.0	2.0	LSB
$ E_O $	Offset error ¹⁾		0.15	1.0	
$ E_G $	Gain error ¹⁾		0.97	1.1	
$ E_D $	Differential linearity error ¹⁾		0.7	1.0	
$ E_L $	Integral linearity error ¹⁾		0.76	1.5	

1. ADC accuracy vs. negative injection current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. The effect of negative injection current on robust pins is specified in [Section 4.3.5](#). Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 4.3.5](#) does not affect the ADC accuracy.
2. Calibration is needed once after each power-up.

Figure 21. ADC accuracy characteristics

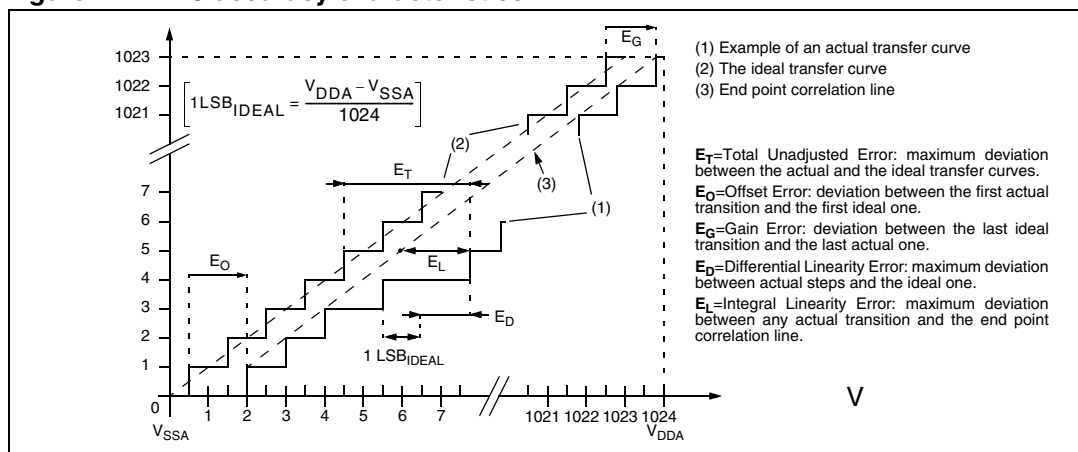
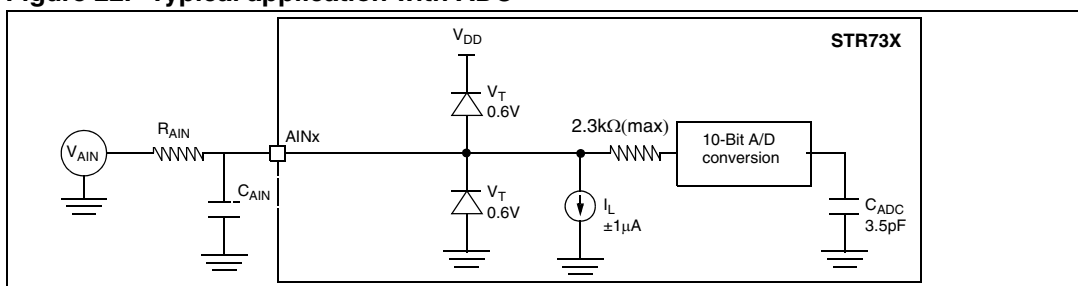


Figure 22. Typical application with ADC



5 Package characteristics

5.1 Package mechanical data

Figure 24. 100-pin thin quad flat package

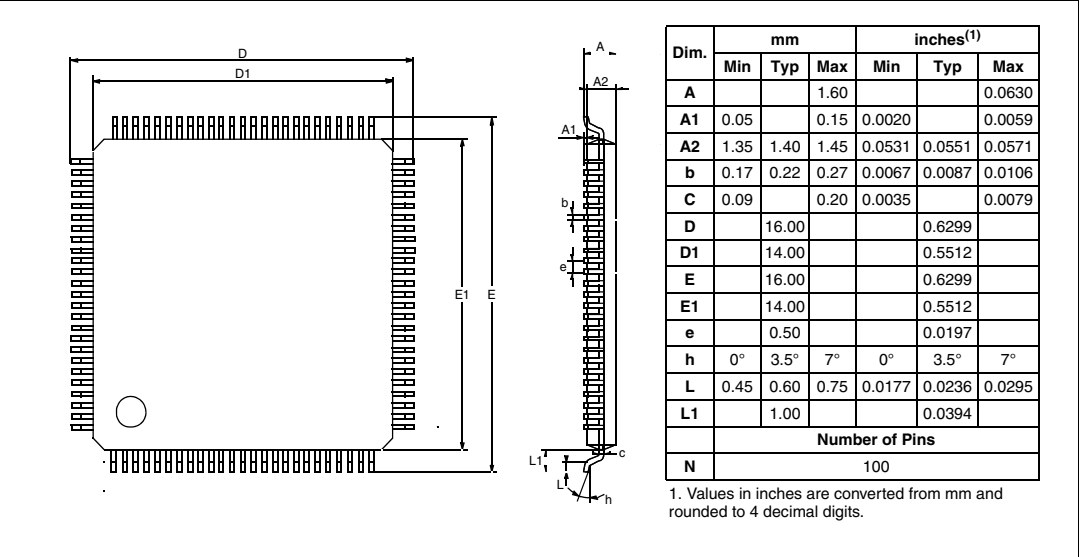


Figure 25. 144-pin thin quad flat package

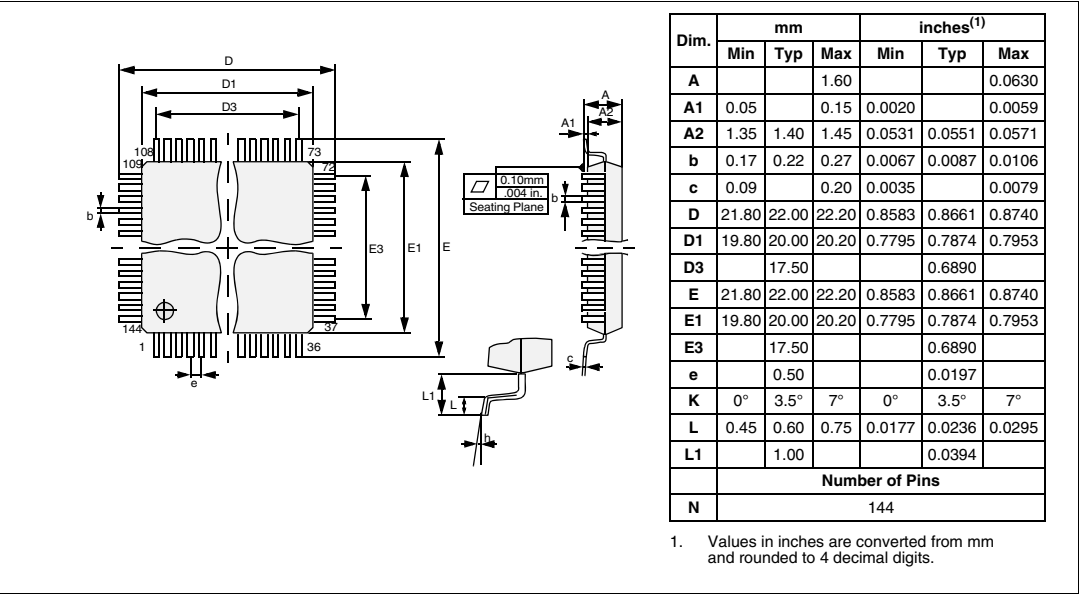


Figure 26. 144-ball low profile fine pitch ball grid array package

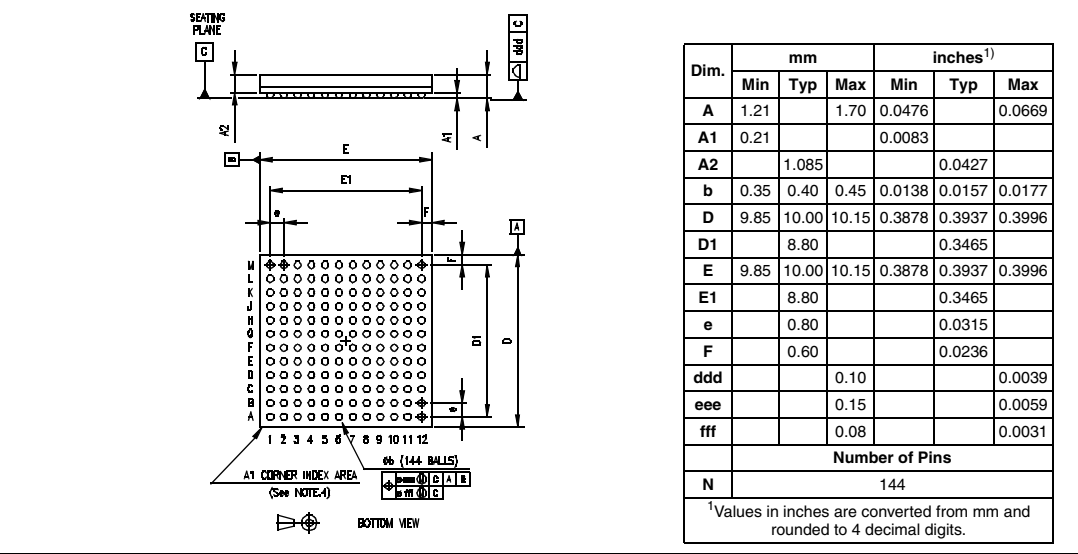
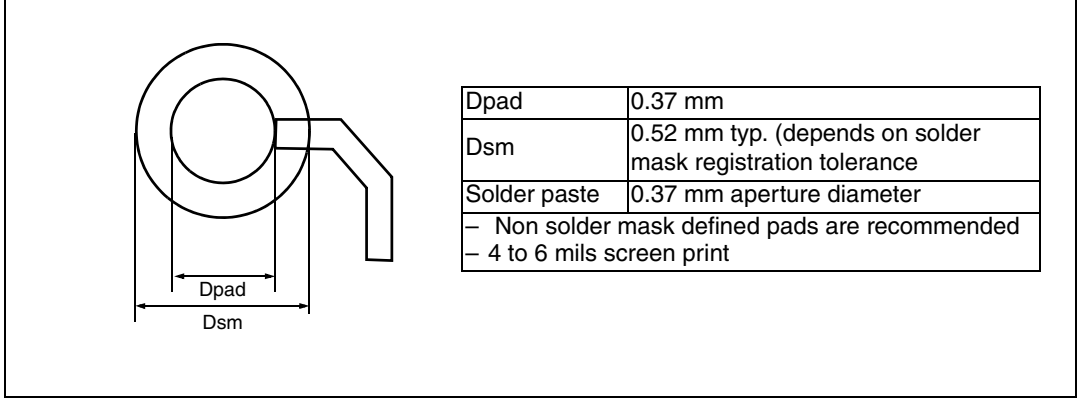


Figure 27. Recommended PCB design rules (0.80/0.75mm pitch BGA)



8 Revision history

Table 30. Document revision history

Date	Revision	Description of changes
19-Sep-2005	1	First release
02-Nov-2005	2	Removed Table 8 power consumption in LP modes Updated PLL frequency in Section 1.1 and Table 12
08-Mar-2006	3	Section 3.4: Preliminary power consumption data updated Section 3.5: DC electrical characteristics updated Section 7: Known limitations added
04-Jun-2006	4	Section 4: Electrical parameters updated Section 7: Known limitations updated Added temperature range -40°C to 85°C in Section 6: Order codes
19-Jun-2006	5	Changed Flash data retention to 20 years at 85°C in Table 18 on page 34 .
08-Sep-2006	6	Changed Table 24: Output driving current on page 39 Added Figure 14: VOL standard ports vs IOL @ VDD 5 V thru Figure 18: VOL P6.0 pin vs IOL @ VDD 5 V on page 40 . Added Figure 20: NRSTIN RPU vs. VDD
08-Jun-2008	7	Inch values rounded to 4 decimal digits in Section 5.1: Package mechanical data Modified BSPI speed in Section 2.1: On-chip peripherals

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